

L Number	Hits	Search Text	DB	Time stamp
-	87	(gate near line).clm. and electrode.clm. and (gate near (dielectric or insulating)).clm. and (semiconductor near (layer or film)).clm. and (ohmic near contact).clm. and ((data or signal) near line).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 10:50
-	80	(gate near line).clm. and electrode.clm. and (gate near (dielectric or insulating)).clm. and (semiconductor near (layer or film)).clm. and (ohmic near contact).clm. and ((data or signal) near line).clm. and source.clm. and drain.clm. and pixel.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 10:51
-	76	(gate near line).clm. and electrode.clm. and (gate near (dielectric or insulating)).clm. and (semiconductor near (layer or film)).clm. and (ohmic near contact).clm. and ((data or signal) near line).clm. and source.clm. and drain.clm. and pixel.clm. and (pixel near electrode).clm. and (drain near electrode).clm. and (source near electrode).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 10:51
-	70	(gate near line).clm. and electrode.clm. and (gate near (dielectric or insulating)).clm. and (semiconductor near (layer or film)).clm. and (ohmic near contact).clm. and ((data or signal) near line).clm. and source.clm. and drain.clm. and pixel.clm. and (pixel near electrode).clm. and (drain near electrode).clm. and (source near electrode).clm. and (ohmic near contact near (layer or film)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 10:52
-	70	(gate near line).clm. and electrode.clm. and (gate near (dielectric or insulating) near (film or layer)).clm. and (semiconductor near (layer or film)).clm. and (ohmic near contact).clm. and ((data or signal) near line).clm. and source.clm. and drain.clm. and pixel.clm. and (pixel near electrode).clm. and (drain near electrode).clm. and (source near electrode).clm. and (ohmic near contact near (layer or film)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 10:52

-	34	(gate near line).clm. and electrode.clm. and (gate near (dielectric or insulating) near (film or layer)).clm. and (semiconductor near (layer or film)).clm. and (ohmic near contact).clm. and ((data or signal) near line).clm. and source.clm. and drain.clm. and pixel.clm. and (pixel near electrode).clm. and (drain near electrode).clm. and (source near electrode).clm. and (ohmic near contact near (layer or film)).clm. and (drain near10 ohmic).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 10:53
-	34	(gate near line).clm. and electrode.clm. and (gate near (dielectric or insulating) near (film or layer)).clm. and (semiconductor near (layer or film)).clm. and (ohmic near contact).clm. and ((data or signal) near line).clm. and source.clm. and drain.clm. and pixel.clm. and (pixel near electrode).clm. and (drain near electrode).clm. and (source near electrode).clm. and (ohmic near contact near (layer or film)).clm. and (drain near10 ohmic).clm. and (source near10 ohmic).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 10:53
-	30	(gate near line).clm. and electrode.clm. and (gate near (dielectric or insulating) near (film or layer)).clm. and (semiconductor near (layer or film)).clm. and (ohmic near contact).clm. and ((data or signal) near line).clm. and source.clm. and drain.clm. and pixel.clm. and (pixel near electrode).clm. and (drain near electrode).clm. and (source near electrode).clm. and (ohmic near contact near (layer or film)).clm. and (drain near10 ohmic).clm. and (source near10 ohmic).clm. and (((data or signal) near line) near10 (gate near line)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 10:53
-	30	(gate near line).clm. and electrode.clm. and (gate near (dielectric or insulating) near (film or layer)).clm. and (semiconductor near (layer or film)).clm. and (ohmic near contact).clm. and ((data or signal) near line).clm. and source.clm. and drain.clm. and pixel.clm. and (pixel near electrode).clm. and (drain near electrode).clm. and (source near electrode).clm. and (ohmic near contact near (layer or film)).clm. and (drain near10 ohmic).clm. and (source near10 ohmic).clm. and (((data or signal) near line) near10 (gate near line)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 10:55

-	3	(gate near line).clm. and electrode.clm. and (gate near (dielectric or insulating) near (film or layer)).clm. and (semiconductor near (layer or film)).clm. and (ohmic near contact).clm. and ((data or signal) near line).clm. and source.clm. and drain.clm. and pixel.clm. and (pixel near electrode).clm. and (drain near electrode).clm. and (source near electrode).clm. and (ohmic near contact near (layer or film)).clm. and (drain near10 ohmic).clm. and (source near10 ohmic).clm. and (((data or signal) near line) near10 (gate near line)).clm. and uneven.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 10:56
-	3	(gate near line).clm. and electrode.clm. and (gate near (dielectric or insulating) near (film or layer)).clm. and (semiconductor near (layer or film)).clm. and (ohmic near contact).clm. and ((data or signal) near line).clm. and source.clm. and drain.clm. and pixel.clm. and (pixel near electrode).clm. and (drain near electrode).clm. and (source near electrode).clm. and (ohmic near contact near (layer or film)).clm. and (drain near10 ohmic).clm. and (source near10 ohmic).clm. and (((data or signal) near line) near10 (gate near line)).clm. and uneven.clm. and ((gate near line) same electrode same (ohmic near contact) same source same drain same data).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 10:57
-	20	(gate near line).clm. and electrode.clm. and (gate near (dielectric or insulating) near (film or layer)).clm. and (semiconductor near (layer or film)).clm. and (ohmic near contact).clm. and ((data or signal) near line).clm. and source.clm. and drain.clm. and pixel.clm. and (pixel near electrode).clm. and (drain near electrode).clm. and (source near electrode).clm. and (ohmic near contact near (layer or film)).clm. and (drain near10 ohmic).clm. and (source near10 ohmic).clm. and (((data or signal) near line) near10 (gate near line)).clm. and ((gate near line) same electrode same (ohmic near contact) same source same drain same data).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 10:57

-	20	(gate near line).clm. and electrode.clm. and (gate near (dielectric or insulating) near (film or layer)).clm. and (semiconductor near (layer or film)).clm. and (ohmic near contact).clm. and ((data or signal) near line).clm. and source.clm. and drain.clm. and pixel.clm. and (pixel near electrode).clm. and (drain near electrode).clm. and (source near electrode).clm. and (ohmic near contact near (layer or film)).clm. and (drain near10 ohmic).clm. and (source near10 ohmic).clm. and (((data or signal) near line) near10 (gate near line)).clm. and ((gate near line) same electrode same (ohmic near contact) same source same drain same (data near line)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 10:57
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L Number	Hits	Search Text	DB	Time stamp
-	10	((drain electrode) near10 (uneven near width))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 11:05
-	3	((drain near electrode) near10 (uneven near width))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 11:05
-	31	((drain near electrode) near10 (uneven))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 11:06
-	14	((drain near electrode) near10 (uneven)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 11:08
-	31	((drain near electrode) near10 (uneven))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 11:08
-	15	((drain near electrode) near5 (uneven))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 11:09
-	148	((drain) near5 (uneven))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 11:09
-	7	((drain) near5 (uneven)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 11:09